SN74AHCT1G04 Single Inverter Gate

1 Features

- Operating range 4.5V to 5.5V
- Max t_{pd} of 7.5ns at 5V
- Low power consumption, 10µA max I_{CC}
- ±8mA output drive at 5V
- Inputs are TTL-voltage compatible
- Latch-up performance exceeds 250mA per JESD 17

2 Applications

- Notebook PCs
- Electronic Points of Sale
- Patient Monitoring
- Motor Controls: AC Induction
- Network Switches
- Tests

3 Description

The SN74AHCT1G04 contains one gate. The device performs the Boolean function Y = $\overline{A}$.

Package Information

PART NUMBER	PACKAGE(1)	PACKAGE SIZE(2)	BODY SIZE(3)
SN74AHCT1G04	DBV (SOT-23, 5)	2.8mm x 2.8mm	2.9mm × 1.6mm
	DCK (SC-70, 5)	2.00mm x 1.25mm	2.00mm × 1.25mm

(1) For more information, see Section 11.
(2) The package size (length × width) is a nominal value and includes pins, where applicable.
(3) The body size (length × width) is a nominal value and does not include pins.

Simplified Schematic

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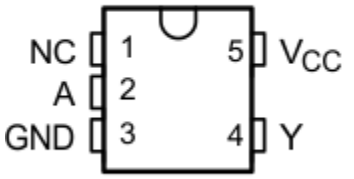
4 Pin Configuration and Functions

DBV OR DCK PACKAGE
(TOP VIEW)



NC – No internal connection

Table 4-1. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NO.	NAME		
1	NC	—	No Connection
2	A	I	Input A
3	GND	—	Ground Pin
4	Y	O	Output Y
5	V_{CC}	—	Power Pin

(1) Signal Types: I = Input, O = Output, I/O = Input or Output

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.5	7	V
V_I (2)	Input voltage range		–0.5	7	V
V_O (2)	Output voltage range		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < 0		–20	mA
I_{OK}	Output clamp current	V_O < 0 or V_O > V_{CC}		±20	mA
I_O	Continuous output current	V_O = 0 to V_{CC}		±25	mA
	Continuous current through V_{CC} or GND			±50	mA
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Section 5.3* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	±1500	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

		MIN(1)	MAX	UNIT
V_{CC}	Supply voltage	4.5	5.5	V
V_{IH}	High-level input voltage	2		V
V_{IL}	Low-level Input voltage		0.8	V
V_I	Input voltage	0	5.5	V
V_O	Output voltage	0	V_{CC}	V
I_{OH}	High-level output current		–8	mA
I_{OL}	Low-level output current		8	mA
Δt/Δv	Input Transition rise or fall rate		20	ns/V
T_A	Operating free-air temperature	–40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs* (SCBA004)

5.4 Thermal Information

THERMAL METRIC(1)		SN74AHCT1G04		UNIT
		DBV	DCK	
		5 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	278	289.2	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	180.5	205.8	
$R_{\theta JB}$	Junction-to-board thermal resistance	184.4	176.2	
ψ_{JT}	Junction-to-top characterization parameter	115.4	117.6	
ψ_{JB}	Junction-to-board characterization parameter	183.4	175.1	
$R_{\theta JC(bot)}$	Junction-to-case (bot) thermal resistance	N/A	N/A	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report (SPRA953).

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}	T_A = 25°C			–40°C to 85°C		–40°C to 125°C		UNIT
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
V_{OH}	High level output voltage	I_{OH} = –50 µA	4.5 V	4.4	4.5		4.4		4.4		V
		I_{OH} = –8 mA		3.94			3.8		3.8		
V_{OL}	Low level output voltage	I_{OL} = 50 µA	4.5 V			0.1		0.1		0.1	V
		I_{OL} = 8 mA				0.36		0.44		0.44	
I_I	Input leakage current	V_I = 5.5 V or GND	0 V to 5.5 V			±0.1		±1		±1	µA
I_{CC}	Supply current	V_I = V_{CC} or GND, I_O = 0	5.5 V			1		10		10	µA
ΔI_{CC} (1)	Supply-Current Change	One input at 3.4 V, Other Inputs at V_{CC} or GND	5.5 V			1.35		1.5		1.5	mA
C_i	Input Capacitance	V_I = V_{CC} or GND	5 V		4			10		10	pF

(1) This is the increase in supply current for each input at one of the specified TTL voltage levels, rather than 0 V or V_{CC}.

5.6 Switching Characteristics

over recommended operating free-air temperature range, V_{CC} = 5 V ± 0.5 V (unless otherwise noted) (see Load Circuit And Voltage Waveforms)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	OUTPUT CAPACITANCE	T_A = 25°C		–40°C to 85°C		–40°C to 125°C		UNIT
				TYP	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A or B	Y	C_L = 15 pF	4.7		1	7.5	1	8	ns
t_{PHL}				4.7		1	7.5	1	8	
t_{PLH}	A or B	Y	C_L = 50 pF	5.5		1	8.5	1	9	ns
t_{PHL}				5.5		1	8.5	1	9	

5.7 Operating Characteristics

V_{CC} = 5 V, T_A = 25°C

PARAMETER		TEST CONDITIONS		TYP	UNIT
C_{pd}	Power dissipation capacitance	No load,	f = 1 MHz	14	pF

5.8 Typical Characteristics

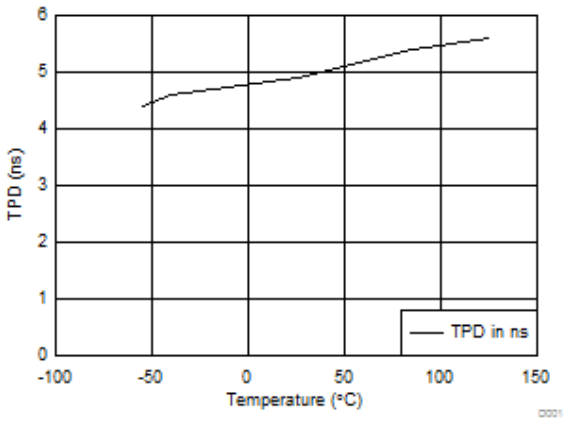
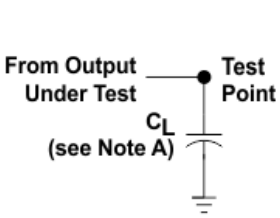
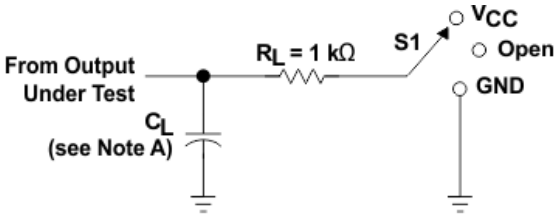


Figure 5-1. TPD vs Temperature

6 Parameter Measurement Information

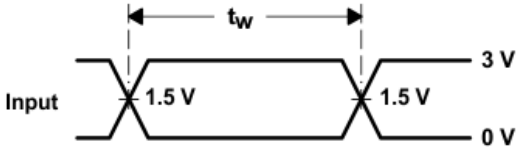


LOAD CIRCUIT FOR
TOTEM-POLE OUTPUTS

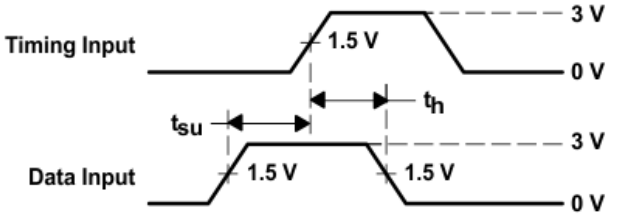


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{CC}
t_{PHZ}/t_{PZH}	GND
Open Drain	V_{CC}

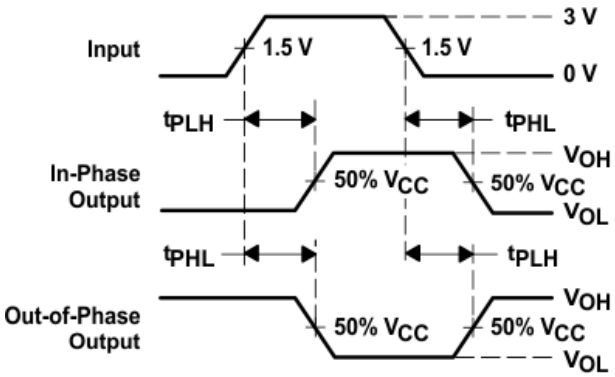
LOAD CIRCUIT FOR
3-STATE AND OPEN-DRAIN OUTPUTS



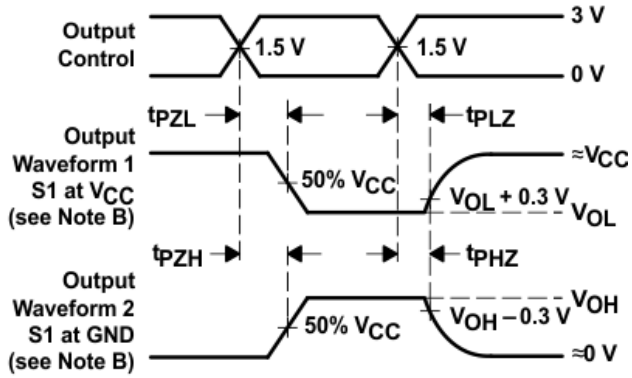
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.
Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r ≤ 3 ns, t_f ≤ 3 ns.
D. The outputs are measured one at a time with one input transition per measurement.
E. All parameters and waveforms are not applicable to all devices.

Figure 6-1. Load Circuit And Voltage Waveforms

7 Detailed Description

7.1 Overview

The SN74AHCT1G04 device contains one inverter. This device has TTL input levels that allow up translation from 3.3 V to 5 V.

7.2 Functional Block Diagram

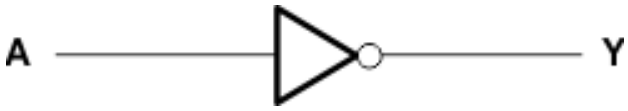


Figure 7-1. Logic Diagram (Positive Logic)

7.3 Feature Description

- V_{CC} is optimized at 5 V
- Allows up voltage translation from 3.3 V to 5 V
  - Inputs accept V_{IH} levels of 2 V
- Slow edge rates minimize output ringing
- Inputs are TTL-Voltage compatible

7.4 Device Functional Modes

Table 7-1. Function Table

INPUT(1) A	OUTPUT(2) Y
H	L
L	H

(1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care
(2) H = Driving High, L = Driving Low, Z = High Impedance State

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

SN74AHCT1G04 is a low-drive CMOS device that can be used for a multitude of inverting type applications where output ringing is a concern. The low drive and slow edge rates will minimize overshoot and undershoot on the outputs. The input switching levels have been lowered to accommodate TTL inputs of 0.8 V $V_{IL}$and 2 V V_{IH}. This feature makes it Ideal for translating up from 3.3 V to 5 V. Figure 8-2 shows this type of translation.

8.2 Typical Application

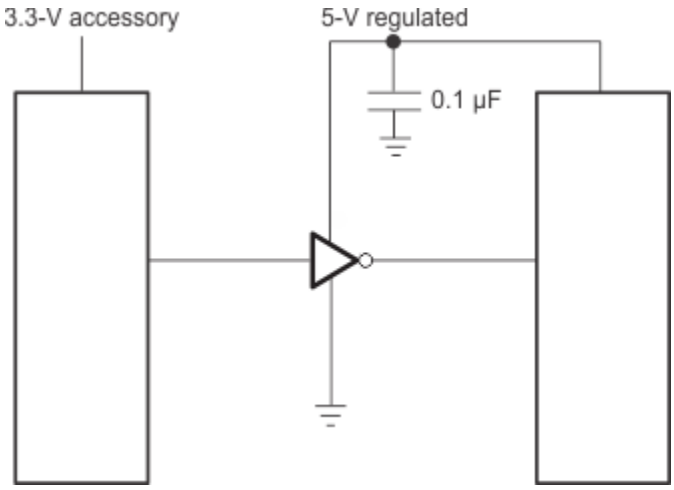


Figure 8-1. Typical Application Schematic

8.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads, so routing and load conditions should be considered to prevent ringing.

8.2.2 Detailed Design Procedure

1. Recommended Input Conditions
   - For rise time and fall time specifications, see Δt/ΔV in the *Section 5.3* table.
   - For specified High and low levels, see V_{IH} and V_{IL} in the *Section 5.3* table.
   - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V_{CC}.
2. Recommend Output Conditions
   - Load currents should not exceed 25 mA per output and 50 mA total for the part.
   - Outputs should not be pulled above V_{CC}.

8.2.3 Application Curves

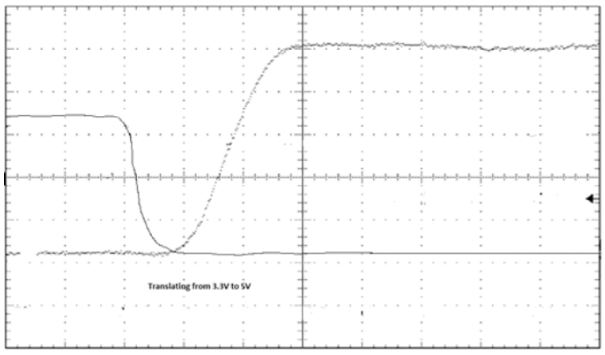


Figure 8-2. 3.3-V to 5-V Translation

8.3 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the *Section 5.3* table.

Each V_{CC} pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1 µF is recommended. If there are multiple V_{CC} pins, 0.01 µF or 0.022 µF is recommended for each power pin. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. A 0.1 µF and 1 µF are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

8.4 Layout

8.4.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4-buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in Figure 8-3 are rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC}, whichever makes more sense or is more convenient. It is acceptable to float outputs unless the part is a transceiver. If the transceiver has an output enable pin, it will disable the outputs section of the part when asserted. This will not disable the input section of the I/Os so they also cannot float when disabled.

8.4.1.1 Layout Example

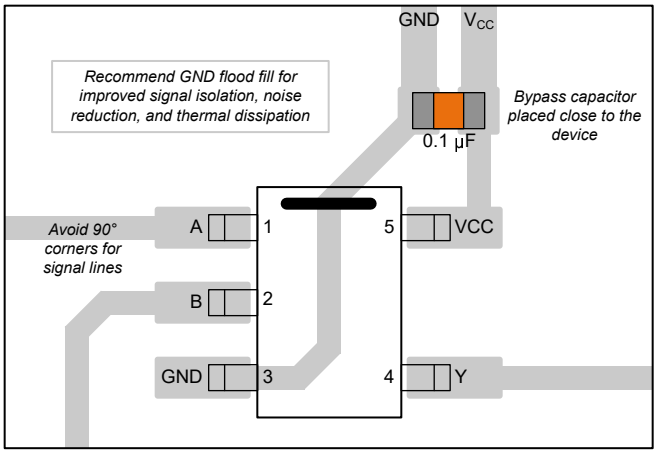


Figure 8-3. Layout Diagram

9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *CMOS Power Consumption and Cpd Calculation* application note
- Texas Instruments, *Designing With Logic* application note
- Texas Instruments, *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices* application note
- Texas Instruments, *Implications of Slow or Floating CMOS Inputs* application note

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

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ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

Changes from Revision Q (October 2023) to Revision R (February 2024)	Page
• Updated thermal values for DBV package from RθJA = 208.2 to 278, RθJC(top) = 76.1 to 180.5, RθJB = 52.5 to 184.4, ΨJT = 4 to 115.4, ΨJB = 51.8 to 183.4, RθJC(bot) = N/A, all values in °C/W	5

Changes from Revision P (December 2014) to Revision Q (October 2023)	Page
• Updated the numbering format for tables, figures, and cross-references throughout the document	1
• Updated thermal values for DCK package from RθJA = 287.6 to 289.2, RθJC(top) = 97.7 to 205.8, RθJB = 65 to 176.2, ΨJT = 2 to 117.6, ΨJB = 64.2 to 175.1, RθJC(bot) = N/A, all values in °C/W	5

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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